

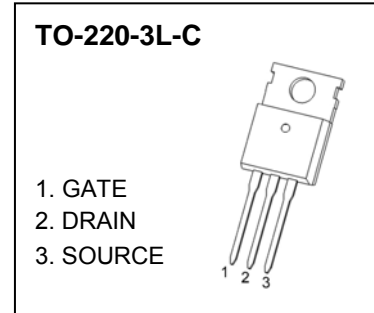


**TO-220-3L-C Plastic-Encapsulate MOSFETS**

**CJP15H03 N-Channel Power MOSFET**

**DESCRIPTION**

The CJP15H03 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.



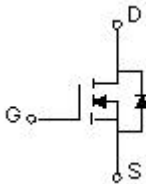
**FEATURES**

- High density cell design for ultra low  $R_{DS(ON)}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

**APPLICATIONS**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

**EQUIVALENT CIRCUIT**



**MAXIMUM RATINGS (  $T_a=25^\circ\text{C}$  unless otherwise noted )**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	150	A
Pulsed Drain Current	$I_{DM}$	600	A
Single Pulsed Avalanche Energy	$E_{AS}^{(1)}$	1700	mJ
Power Dissipation	$P_D$	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	$T_L$	260	$^\circ\text{C}$

(1). $E_{AS}$  condition:  $V_{DD}=20\text{V}$ ,  $L=1\text{mH}$ ,  $R_G=25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

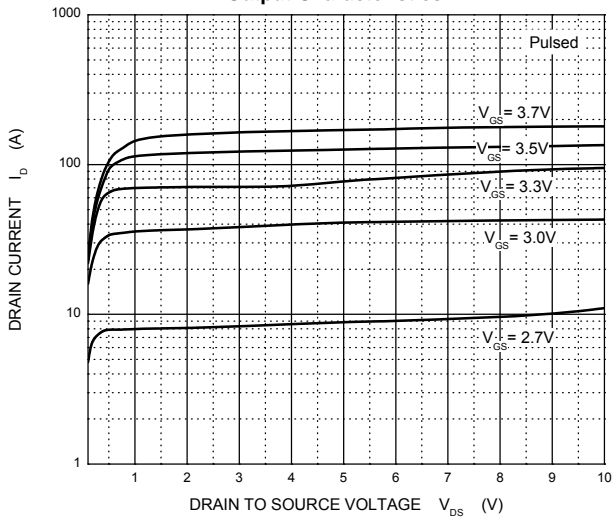
**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
<b>On characteristics (note1)</b>						
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2		2.5	V
Static drain-source on-state resistance	R <sub>Ds(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		2.3	3	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		3.2	4	mΩ
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	32			S
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f =1MHz		5000		pF
Output capacitance	C <sub>oss</sub>			1135		
Reverse transfer capacitance	C <sub>rss</sub>			563		
<b>Switching characteristics (note 2)</b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A		38		nC
Gate-source charge	Q <sub>gs</sub>			9		
Gate-drain charge	Q <sub>gd</sub>			13		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =2A V <sub>GS</sub> =10V, R <sub>G</sub> =2.5Ω, R <sub>L</sub> =15Ω		26		ns
Turn-on rise time	t <sub>r</sub>			24		
Turn-off delay time	t <sub>d(off)</sub>			91		
Turn-off fall time	t <sub>f</sub>			39		
<b>Drain-Source Diode Characteristics</b>						
Drain-source diode forward voltage(note1)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =150A			1.2	V
Continuous drain-source diode forward current (note3)	I <sub>S</sub>				150	A
Pulsed drain-source diode forward current	I <sub>SM</sub>				600	A

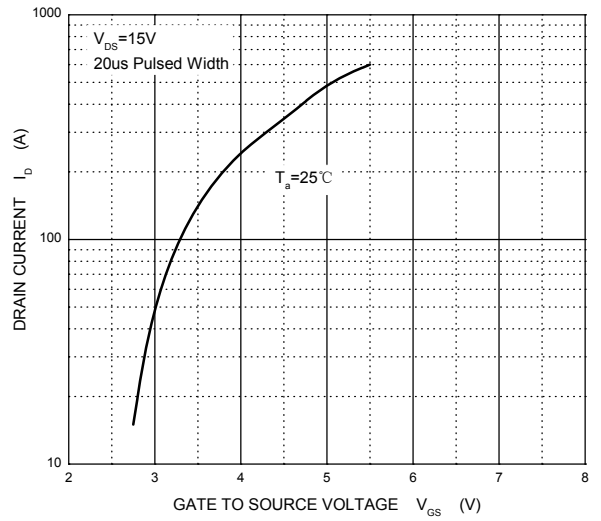
Notes:

1. Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.
2. Guaranteed by design, not subject to production.
3. Surface Mounted on FR4 Board, t≤10 sec.

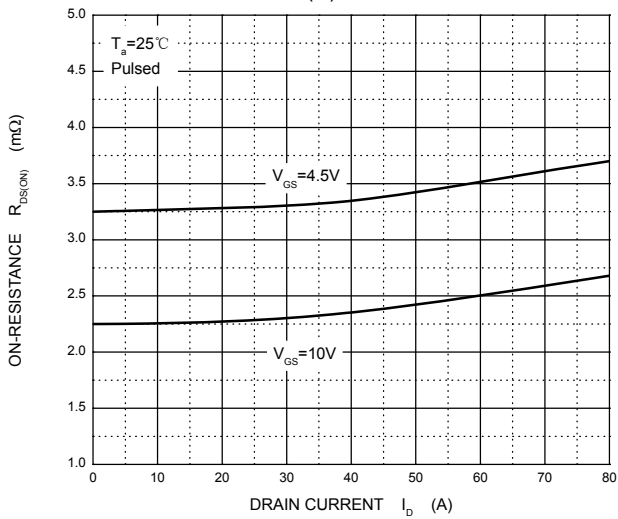
### Output Characteristics



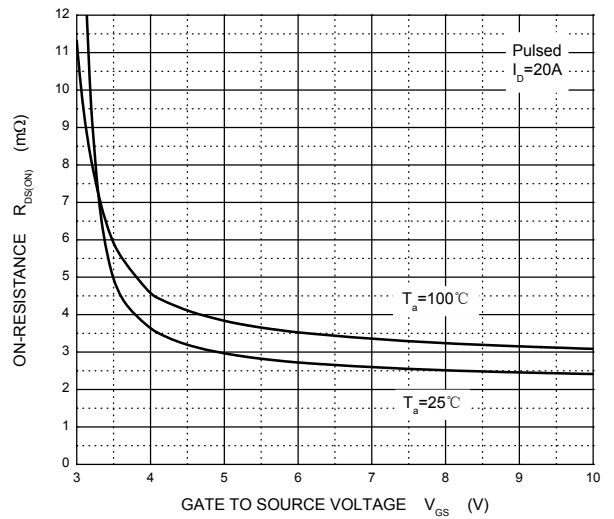
### Transfer Characteristics



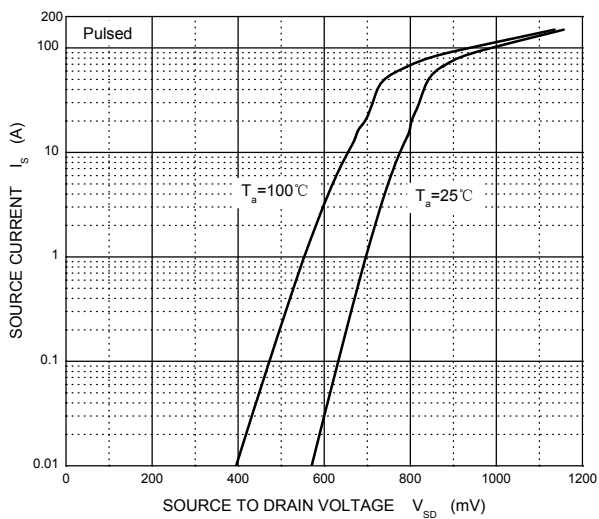
### $R_{DS(ON)}$ — $I_D$



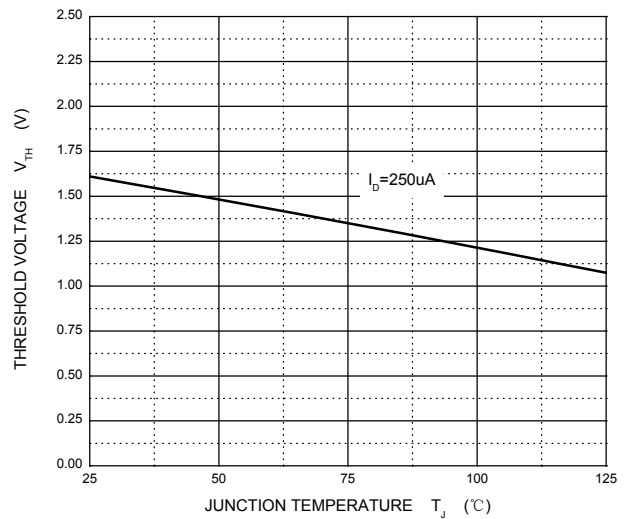
### $R_{DS(ON)}$ — $V_{GS}$



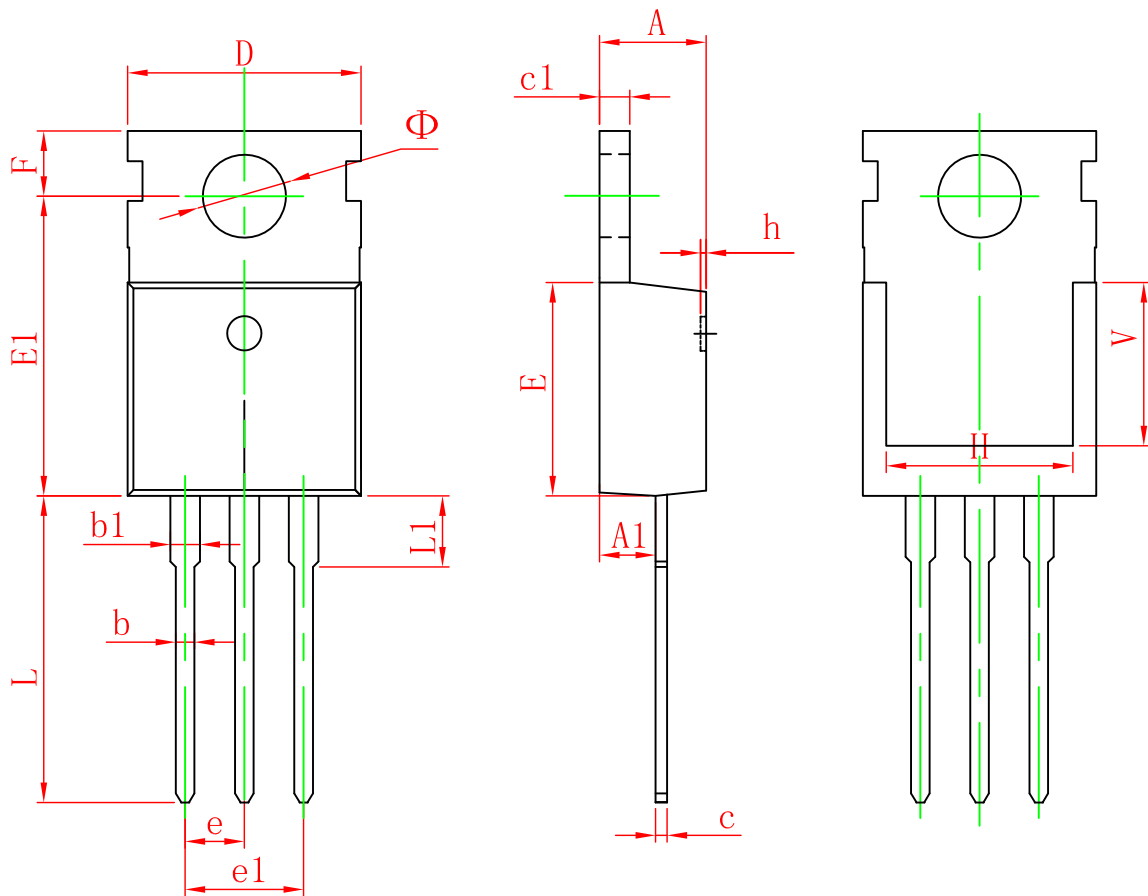
### $I_S$ — $V_{SD}$



### Threshold Voltage



# TO-220-3L-C Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
$\Phi$	3.400	3.800	0.134	0.150